Abstract of the Disclosure:

The novel etching process for a two-layer metallization, or dual damascene patterning, is simple and cost-effective to carry out and reliably prevents fences from forming during the etching process in the region of the polymer intermediate layer. The etching of the oxide layer and of the polymer intermediate layer for the dual damascene patterning is effected by a CF_4 ARC open process with high selectivity with respect to the photoresist with a lengthened etching time.

WHS:kf - Z&PINFN10176F//2/7/2002